Po-Hsun Ho

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/1590027/publications.pdf

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15	717	840776 11	996975 15
papers	citations	h-index	g-index

15	15	15	1676
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	High-Mobility InSe Transistors: The Role of Surface Oxides. ACS Nano, 2017, 11, 7362-7370.	14.6	177
2	Extrinsic Origin of Persistent Photoconductivity in Monolayer MoS2 Field Effect Transistors. Scientific Reports, 2015, 5, 11472.	3.3	110
3	Self-Encapsulated Doping of n-Type Graphene Transistors with Extended Air Stability. ACS Nano, 2012, 6, 6215-6221.	14.6	76
4	Fast growth of large-grain and continuous MoS2 films through a self-capping vapor-liquid-solid method. Nature Communications, 2020, 11, 3682.	12.8	76
5	Selfâ€Crackâ€Filled Graphene Films by Metallic Nanoparticles for Highâ€Performance Graphene Heterojunction Solar Cells. Advanced Materials, 2015, 27, 1724-1729.	21.0	65
6	Surface Oxidation Doping to Enhance Photogenerated Carrier Separation Efficiency for Ultrahigh Gain Indium Selenide Photodetector. ACS Photonics, 2017, 4, 2930-2936.	6.6	44
7	Sunlight-activated graphene-heterostructure transparent cathodes: enabling high-performance n-graphene/p-Si Schottky junction photovoltaics. Energy and Environmental Science, 2015, 8, 2085-2092.	30.8	42
8	Precisely Controlled Ultrastrong Photoinduced Doping at Grapheneâ€“Heterostructures Assisted by Trapâ€Stateâ€Mediated Charge Transfer. Advanced Materials, 2015, 27, 7809-7815.	21.0	39
9	Wavelengthâ€Selective Dual pâ€and nâ€Type Carrier Transport of an Organic/Graphene/Inorganic Heterostructure. Advanced Materials, 2015, 27, 282-287.	21.0	26
10	High-Mobility InSe Transistors: The Nature of Charge Transport. ACS Applied Materials & Interfaces, 2019, 11, 35969-35976.	8.0	23
11	Residue-free fabrication of high-performance graphene devices by patterned PMMA stencil mask. AIP Advances, 2014, 4, .	1.3	11
12	Environment-insensitive and gate-controllable photocurrent enabled by bandgap engineering of MoS2 junctions. Scientific Reports, 2017, 7, 44768.	3.3	11
13	Dependence of Nanocrystal Dimensionality on the Polymer Nanomorphology, Anisotropic Optical Absorption, and Carrier Transport in P3HT:TiO₂ Bulk Heterojunctions. Journal of Physical Chemistry C, 2012, 116, 25081-25088.	3.1	10
14	Observation of quantum Hall plateau-plateau transition and scaling behavior of the zeroth Landau level in graphene<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>p</mml:mi><mml:mtext>â^’</mml:mtext><mml:mi>n</mml:mi></mml:mrow></mml:math> Physical Review B, 2016, 93, .	3.2	5
15	Spatially and Precisely Controlled Large-Scale and Persistent Optical Gating in a TiOxâ€“MoS2 Heterostructure. ACS Applied Materials & Interfaces, 2018, 10, 38319-38325.	8.0	2